

Plasma processing system

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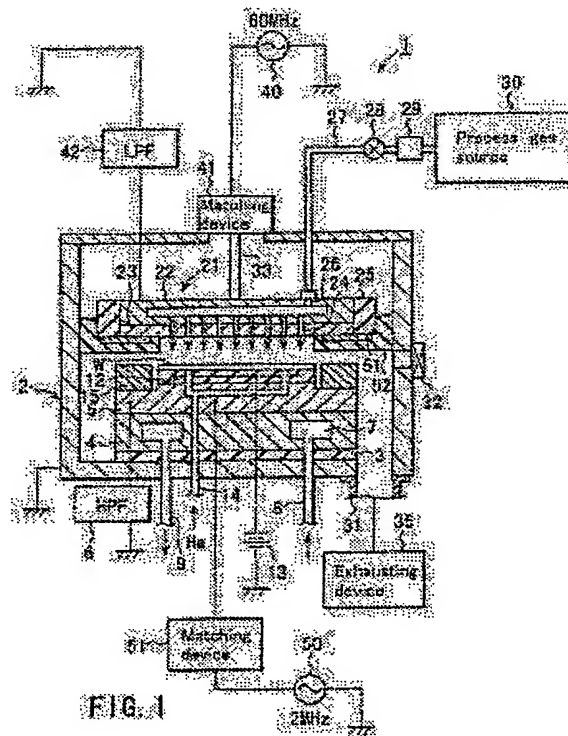
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Abstract of TW 462092 (B)

In a plasma processing system of this invention, a first electrode (21) connected to a high frequency power source (40) is disposed in a chamber, a second electrode (5) disposed opposite to the first electrode, and a substrate (W) to be processed disposed between the electrodes. A high modulating frequency absorbing element (51) is disposed to contact the end portion or peripheral portion of the surface of the first electrode (21) that is opposite to the second electrode (5) so as to absorb the high modulating electric waves of the high frequency power source (4), with a high frequency absorbing element for absorbing the reflected high modulated frequency prior to its return to the high frequency power source. Hence, standing waves caused by high frequencies can be effectively prohibited to result in uniform plasma density.



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